

# BFP840ESD

## SiGe:C NPN RF bipolar transistor



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## Product description

The BFP840ESD is a discrete RF heterojunction bipolar transistor (HBT) with an integrated ESD protection suitable for 5 GHz band applications.



## Feature list

- Unique combination of high end RF performance and robustness: 20 dBm maximum RF input power, 1.5 kV HBM ESD hardness
- High transition frequency  $f_T = 80$  GHz to enable low noise figure at high frequencies:  
 $NF_{\min} = 0.85$  dB at 5.5 GHz, 1.8 V, 5 mA
- High gain  $G_{ms} = 22.5$  dB at 5.5 GHz, 1.8 V, 10 mA
- $OIP_3 = 22$  dBm at 5.5 GHz, 1.8 V, 10 mA
- Suitable for low voltage applications e.g.  $V_{CC} = 1.2$  V and 1.8 V (2.85 V, 3.3 V, 3.6 V require a corresponding collector resistor)

## Product validation

Qualified for industrial applications according to the relevant tests of JEDEC47/20/22.

## Potential applications

- Mobile and fixed connectivity applications: WLAN, WiMAX and UWB
- Satellite communication systems: satellite radio (SDARs, DAB), navigation systems (e.g. GPS, GLONASS, BeiDou, Galileo)

## Device information

**Table 1** Part information

Product name / Ordering code	Package	Pin configuration				Marking	Pieces / Reel
BFP840ESD / BFP840ESDH6327XTSA1	SOT343	1 = B	2 = E	3 = C	4 = E	T8s	3000

**Attention:** ESD (Electrostatic discharge) sensitive device, observe handling precautions

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**Absolute maximum ratings**

**1 Absolute maximum ratings**

**Table 2 Absolute maximum ratings at  $T_A = 25\text{ °C}$  (unless otherwise specified)**

Parameter	Symbol	Values		Unit	Note or test condition
		Min.	Max.		
Collector emitter voltage	$V_{CEO}$	-	2.25	V	Open base
			2.0		$T_A = -55\text{ °C}$ , open base
Collector base voltage <sup>1)</sup>	$V_{CBO}$		2.9		Open emitter
			2.6		$T_A = -55\text{ °C}$ , open emitter
Collector emitter voltage <sup>2)</sup>	$V_{CES}$		2.25		E-B short circuited
			2.0		$T_A = -55\text{ °C}$ , E-B short circuited
Base current	$I_B$	-5	3	mA	-
Collector current	$I_C$	-	35		
RF input power	$P_{RFIn}$	-	20	dBm	
ESD stress pulse	$V_{ESD}$	-1.5	1.5	kV	HBM, all pins, acc. to JESD22-A114
Total power dissipation <sup>3)</sup>	$P_{tot}$	-	75	mW	$T_S \leq 108\text{ °C}$
Junction temperature	$T_J$	-	150	°C	-
Storage temperature	$T_{Stg}$	-55			

**Attention:** *Stresses above the max. values listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Exceeding only one of these values may cause irreversible damage to the integrated circuit.*

<sup>1</sup>  $V_{CBO}$  is similar to  $V_{CEO}$  due to design.

<sup>2</sup>  $V_{CES}$  is identical to  $V_{CEO}$  due to design.

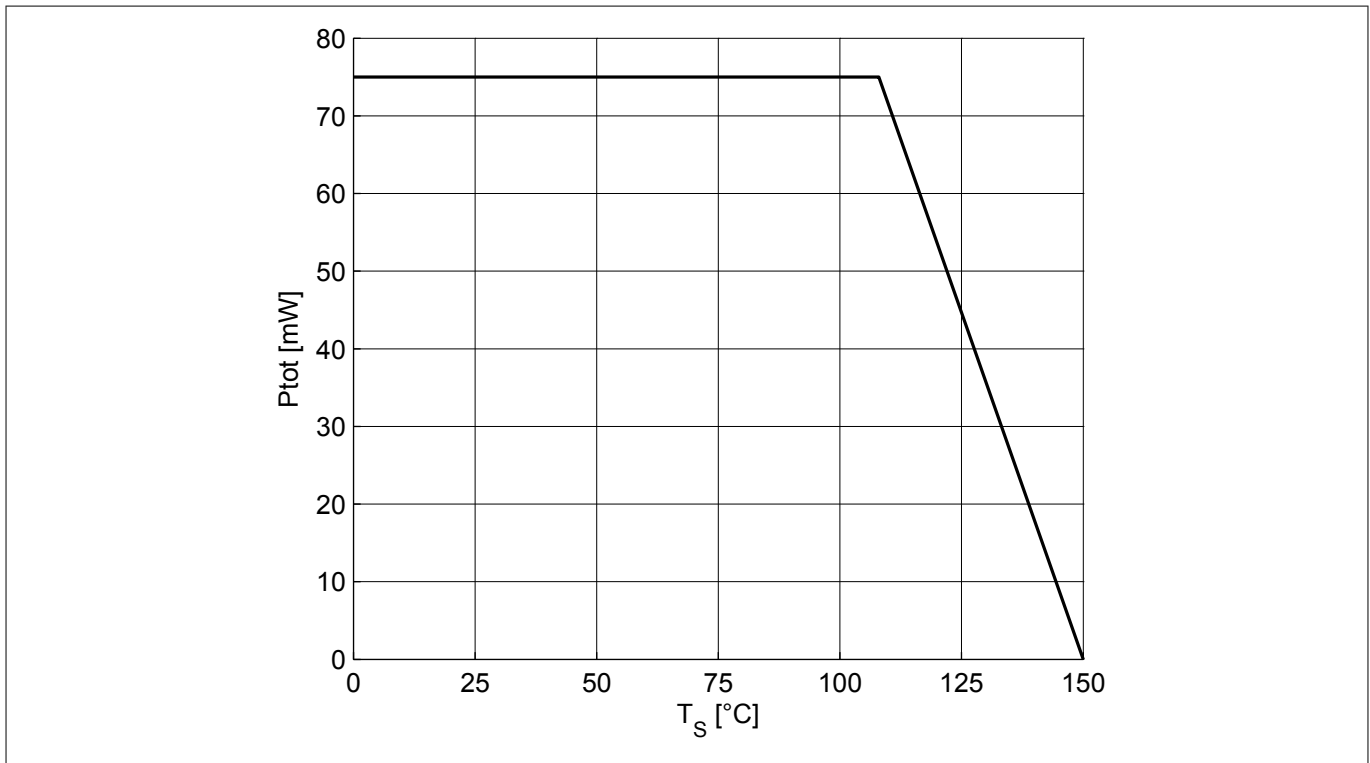
<sup>3</sup>  $T_S$  is the soldering point temperature.  $T_S$  is measured on the emitter lead at the soldering point of the PCB.

**Thermal characteristics**

**2 Thermal characteristics**

**Table 3 Thermal resistance**

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Junction - soldering point	$R_{thJS}$	-	551	-	K/W	-



**Figure 1 Total power dissipation  $P_{tot} = f(T_s)$**

**Electrical characteristics**

**3 Electrical characteristics**

**3.1 DC characteristics**

**Table 4 DC characteristics at  $T_A = 25\text{ °C}$**

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Collector emitter breakdown voltage	$V_{(BR)CEO}$	2.25	2.6	–	V	$I_C = 1\text{ mA}$ , $I_B = 0$ , open base
Collector emitter leakage current	$I_{CES}$	–	–	400 <sup>1)</sup>	nA	$V_{CE} = 1.5\text{ V}$ , $V_{BE} = 0$ , E-B short circuited
Collector base leakage current	$I_{CBO}$			400 <sup>1)</sup>		$V_{CB} = 1.5\text{ V}$ , $I_E = 0$ , open emitter
Emitter base leakage current	$I_{EBO}$			10 <sup>1)</sup>	$\mu\text{A}$	$V_{EB} = 0.5\text{ V}$ , $I_C = 0$ , open collector
DC current gain	$h_{FE}$	150	260	450		$V_{CE} = 1.8\text{ V}$ , $I_C = 10\text{ mA}$ , pulse measured

**3.2 General AC characteristics**

**Table 5 General AC characteristics at  $T_A = 25\text{ °C}$**

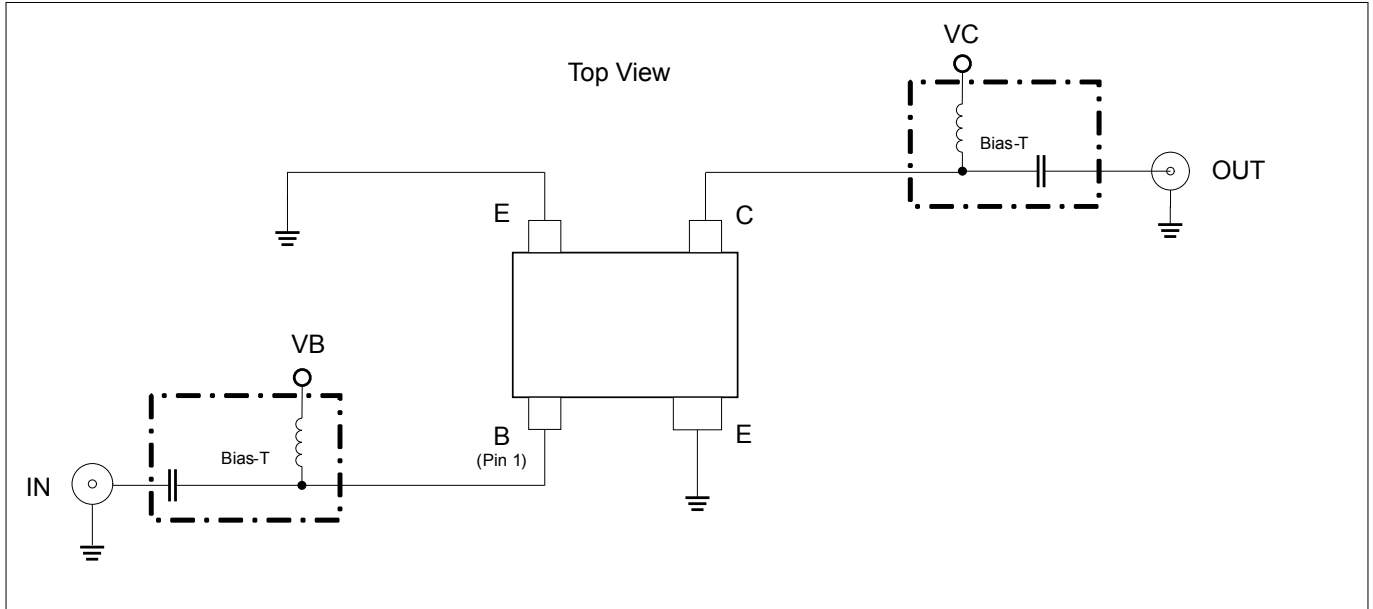
Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Transition frequency	$f_T$	–	80	–	GHz	$V_{CE} = 1.8\text{ V}$ , $I_C = 25\text{ mA}$ , $f = 2\text{ GHz}$
Collector base capacitance	$C_{CB}$		37		fF	$V_{CB} = 1.8\text{ V}$ , $V_{BE} = 0$ , $f = 1\text{ MHz}$ , emitter grounded
Collector emitter capacitance	$C_{CE}$		0.40		pF	$V_{CE} = 1.8\text{ V}$ , $V_{BE} = 0$ , $f = 1\text{ MHz}$ , base grounded
Emitter base capacitance	$C_{EB}$		0.41			$V_{EB} = 0.4\text{ V}$ , $V_{CB} = 0$ , $f = 1\text{ MHz}$ , collector grounded

<sup>1</sup> Maximum values not limited by the device but by the short cycle time of the 100% test

**Electrical characteristics**

**3.3 Frequency dependent AC characteristics**

Measurement setup is a test fixture with Bias-T's in a 50 Ω system,  $T_A = 25\text{ °C}$ .



**Figure 2 Testing circuit**

**Table 6 AC characteristics,  $V_{CE} = 1.8\text{ V}$ ,  $f = 0.45\text{ GHz}$**

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Power gain						
• Maximum power gain	$G_{ms}$	–	33.5	–	dB	$I_C = 10\text{ mA}$
• Transducer gain	$ S_{21} ^2$		27.5			
Noise figure						
• Minimum noise figure	$NF_{min}$	–	0.6	–	dB	$I_C = 5\text{ mA}$
• Associated gain	$G_{ass}$		26.5			
Linearity						
• 3rd order intercept point at output	$OIP_3$	–	19.5	–	dBm	$Z_S = Z_L = 50\text{ }\Omega$ , $I_C = 10\text{ mA}$
• 1 dB gain compression point at output	$OP_{1dB}$		4			

**Electrical characteristics**

**Table 7 AC characteristics,  $V_{CE} = 1.8\text{ V}$ ,  $f = 0.9\text{ GHz}$**

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Power gain						
• Maximum power gain	$G_{ms}$	–	30	–	dB	$I_C = 10\text{ mA}$
• Transducer gain	$ S_{21} ^2$		27			
Noise figure					dB	
• Minimum noise figure	$NF_{min}$	–	0.6	–		$I_C = 5\text{ mA}$
• Associated gain	$G_{ass}$		25.5			
Linearity						
• 3rd order intercept point at output	$OIP_3$	–	19.5	–	dBm	$Z_S = Z_L = 50\ \Omega$ , $I_C = 10\text{ mA}$
• 1 dB gain compression point at output	$OP_{1dB}$		4			

**Table 8 AC characteristics,  $V_{CE} = 1.8\text{ V}$ ,  $f = 1.5\text{ GHz}$**

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Power gain						
• Maximum power gain	$G_{ms}$	–	28	–	dB	$I_C = 10\text{ mA}$
• Transducer gain	$ S_{21} ^2$		25.5			
Noise figure					dB	
• Minimum noise figure	$NF_{min}$	–	0.65	–		$I_C = 5\text{ mA}$
• Associated gain	$G_{ass}$		24			
Linearity						
• 3rd order intercept point at output	$OIP_3$	–	19.5	–	dBm	$Z_S = Z_L = 50\ \Omega$ , $I_C = 10\text{ mA}$
• 1 dB gain compression point at output	$OP_{1dB}$		4			

**Table 9 AC characteristics,  $V_{CE} = 1.8\text{ V}$ ,  $f = 1.9\text{ GHz}$**

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Power gain						
• Maximum power gain	$G_{ms}$	–	27	–	dB	$I_C = 10\text{ mA}$
• Transducer gain	$ S_{21} ^2$		25			
Noise figure					dB	
• Minimum noise figure	$NF_{min}$	–	0.65	–		$I_C = 5\text{ mA}$
• Associated gain	$G_{ass}$		23			
Linearity						
• 3rd order intercept point at output	$OIP_3$	–	21	–	dBm	$Z_S = Z_L = 50\ \Omega$ , $I_C = 10\text{ mA}$
• 1 dB gain compression point at output	$OP_{1dB}$		4.5			

**Electrical characteristics**

**Table 10 AC characteristics,  $V_{CE} = 1.8\text{ V}$ ,  $f = 2.4\text{ GHz}$**

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Power gain						
• Maximum power gain	$G_{ms}$	–	26	–	dB	$I_C = 10\text{ mA}$
• Transducer gain	$ S_{21} ^2$		24			
Noise figure					dB	
• Minimum noise figure	$NF_{min}$	–	0.7	–		$I_C = 5\text{ mA}$
• Associated gain	$G_{ass}$		22			
Linearity						
• 3rd order intercept point at output	$OIP_3$	–	21	–	dBm	$Z_S = Z_L = 50\ \Omega$ , $I_C = 10\text{ mA}$
• 1 dB gain compression point at output	$OP_{1dB}$		4			

**Table 11 AC characteristics,  $V_{CE} = 1.8\text{ V}$ ,  $f = 3.5\text{ GHz}$**

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Power gain						
• Maximum power gain	$G_{ms}$	–	24.5	–	dB	$I_C = 10\text{ mA}$
• Transducer gain	$ S_{21} ^2$		22			
Noise figure					dB	
• Minimum noise figure	$NF_{min}$	–	0.7	–		$I_C = 5\text{ mA}$
• Associated gain	$G_{ass}$		20			
Linearity						
• 3rd order intercept point at output	$OIP_3$	–	22.5	–	dBm	$Z_S = Z_L = 50\ \Omega$ , $I_C = 10\text{ mA}$
• 1 dB gain compression point at output	$OP_{1dB}$		5			

**Table 12 AC characteristics,  $V_{CE} = 1.8\text{ V}$ ,  $f = 5.5\text{ GHz}$**

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Power gain						
• Maximum power gain	$G_{ms}$	–	22.5	–	dB	$I_C = 10\text{ mA}$
• Transducer gain	$ S_{21} ^2$		18.5			
Noise figure					dB	
• Minimum noise figure	$NF_{min}$	–	0.85	–		$I_C = 5\text{ mA}$
• Associated gain	$G_{ass}$		17			
Linearity						
• 3rd order intercept point at output	$OIP_3$	–	22	–	dBm	$Z_S = Z_L = 50\ \Omega$ , $I_C = 10\text{ mA}$
• 1 dB gain compression point at output	$OP_{1dB}$		5			

**Electrical characteristics**

**Table 13 AC characteristics,  $V_{CE} = 1.8 \text{ V}$ ,  $f = 10 \text{ GHz}$**

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Power gain						
• Maximum power gain	$G_{ms}$	–	17	–	dB	$I_C = 10 \text{ mA}$
• Transducer gain	$ S_{21} ^2$		12			
Noise figure						
• Minimum noise figure	$NF_{min}$	–	1.2	–	dB	$I_C = 5 \text{ mA}$
• Associated gain	$G_{ass}$		12.5			
Linearity						
• 3rd order intercept point at output	$OIP_3$	–	19.5	–	dBm	$Z_S = Z_L = 50 \Omega$ , $I_C = 10 \text{ mA}$
• 1 dB gain compression point at output	$OP_{1dB}$		2.5			

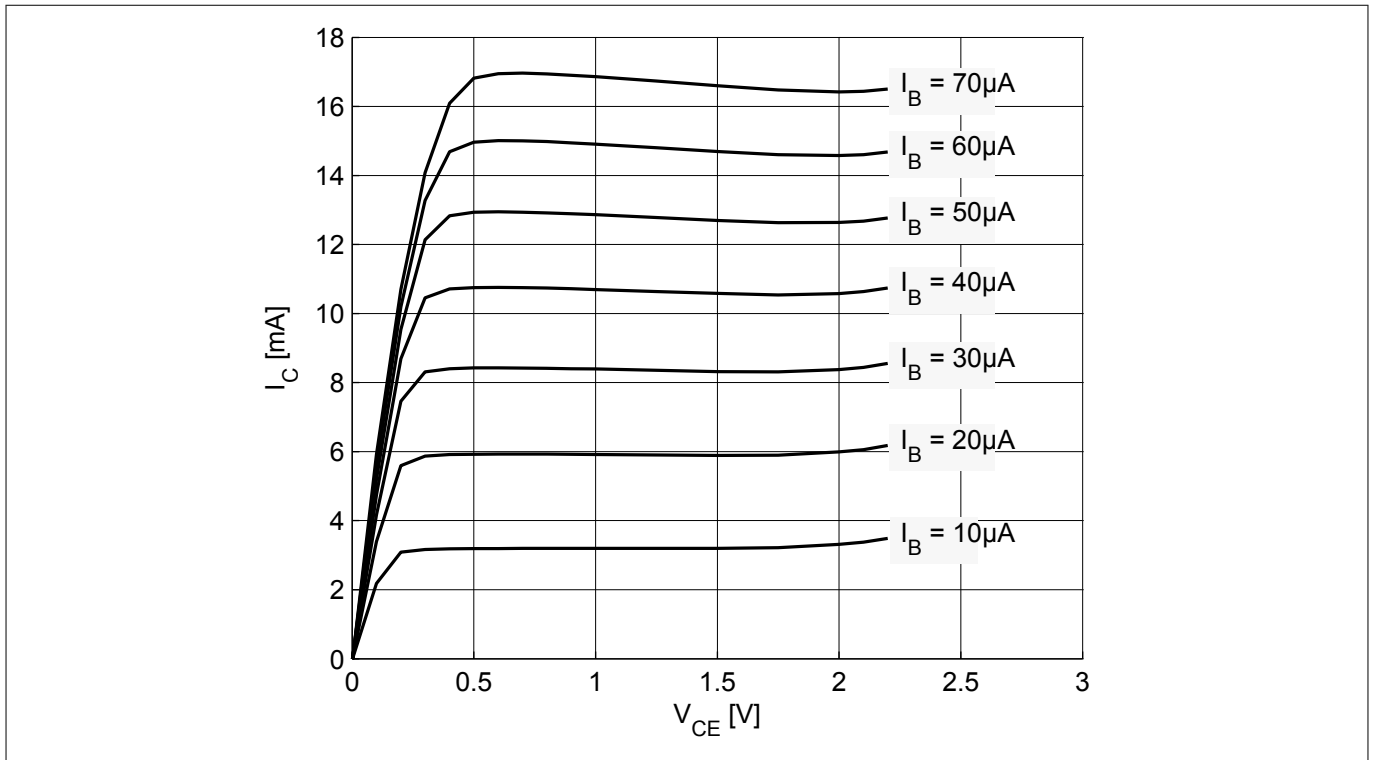
**Table 14 AC characteristics,  $V_{CE} = 1.8 \text{ V}$ ,  $f = 12 \text{ GHz}$**

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Power gain						
• Maximum power gain	$G_{ms}$	–	15.5	–	dB	$I_C = 10 \text{ mA}$
• Transducer gain	$ S_{21} ^2$		9.5			
Noise figure						
• Minimum noise figure	$NF_{min}$	–	1.45	–	dB	$I_C = 5 \text{ mA}$
• Associated gain	$G_{ass}$		11			
Linearity						
• 3rd order intercept point at output	$OIP_3$	–	18.5	–	dBm	$Z_S = Z_L = 50 \Omega$ , $I_C = 10 \text{ mA}$
• 1 dB gain compression point at output	$OP_{1dB}$		1.5			

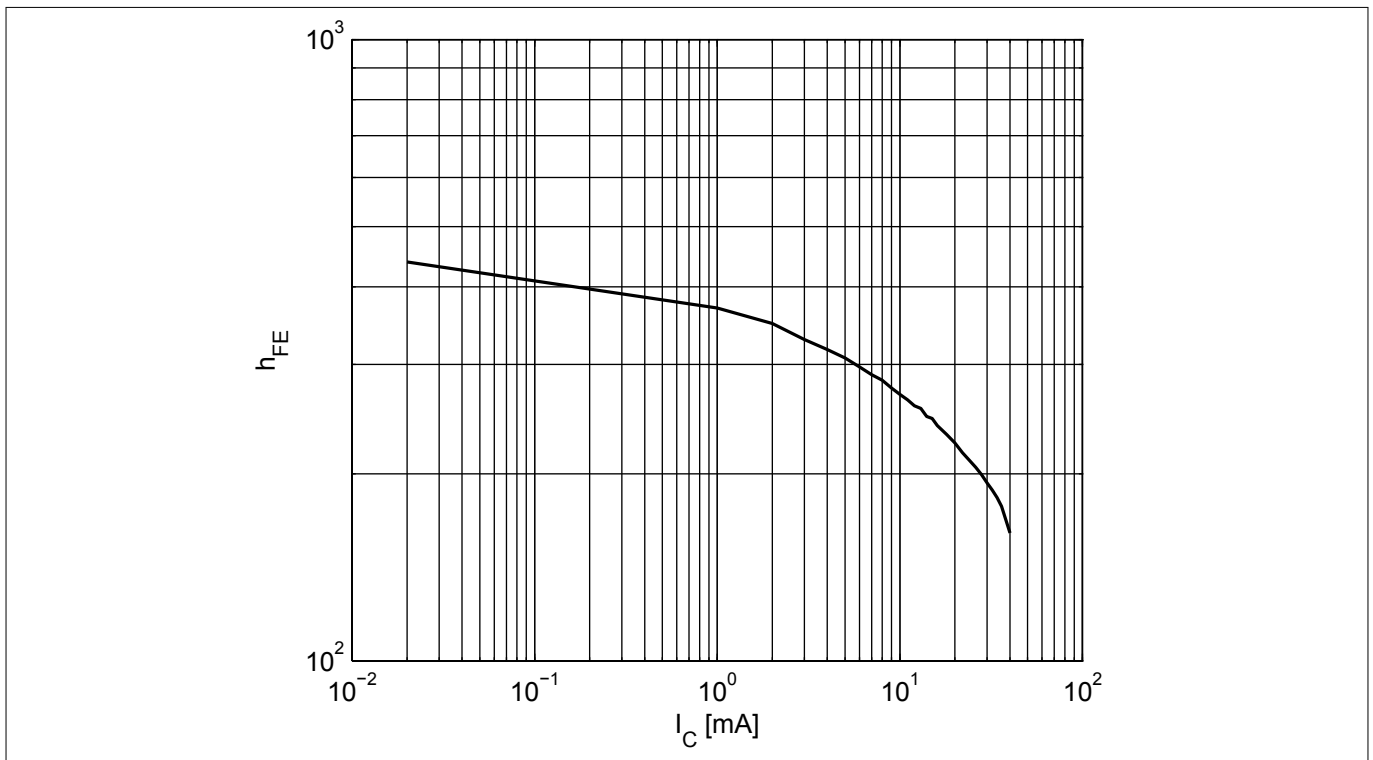
Note:  $G_{ms} = |S_{21} / S_{12}|$  for  $k < 1$ ;  $G_{ma} = |S_{21} / S_{12}| (k - (k^2 - 1)^{1/2})$  for  $k > 1$ . In order to get the  $NF_{min}$  values stated in this chapter, the test fixture losses have been subtracted from all measured results.  $OIP_3$  value depends on termination of all intermodulation frequency components. Termination used for this measurement is  $50 \Omega$  from 0.2 MHz to 12 GHz.

Electrical characteristics

**3.4 Characteristic DC diagrams**

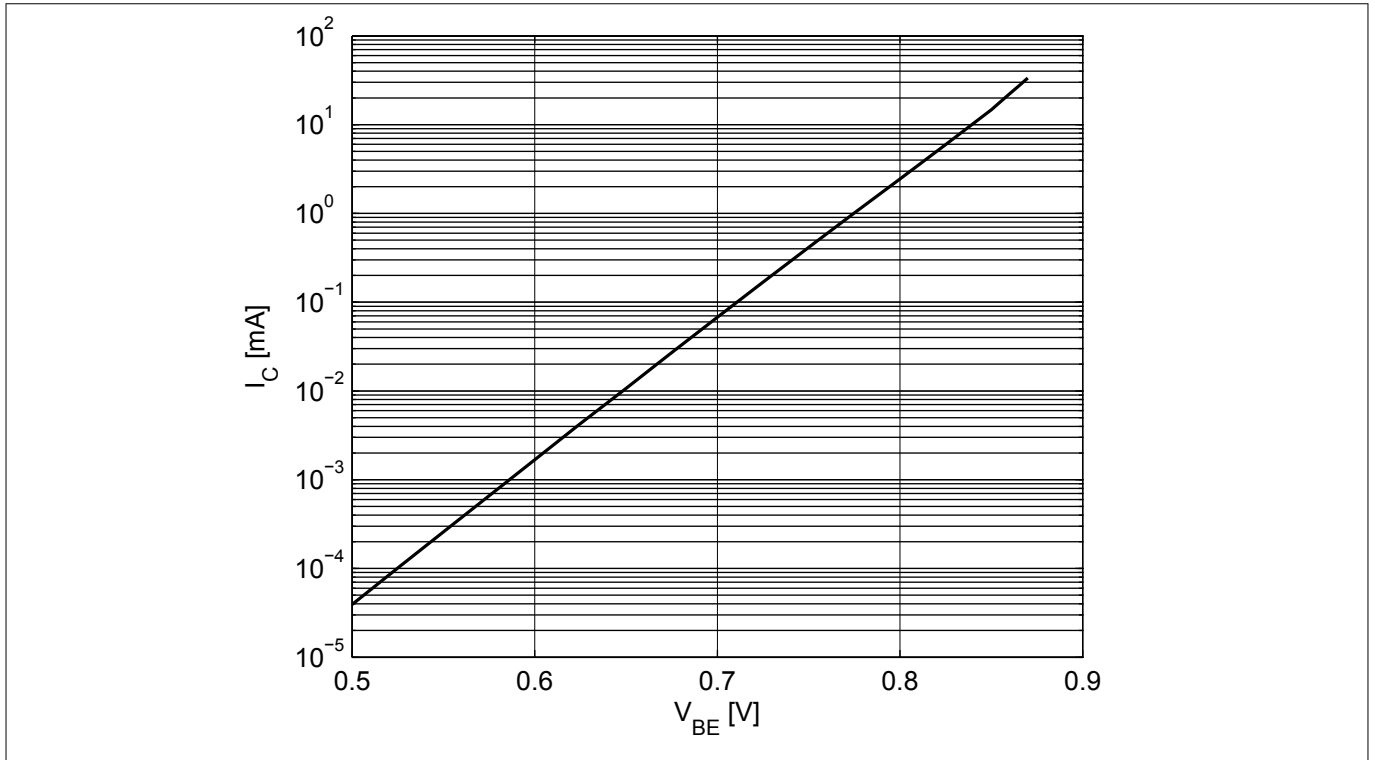


**Figure 3 Collector current vs. collector emitter voltage  $I_C = f(V_{CE})$ ,  $I_B = \text{parameter}$**

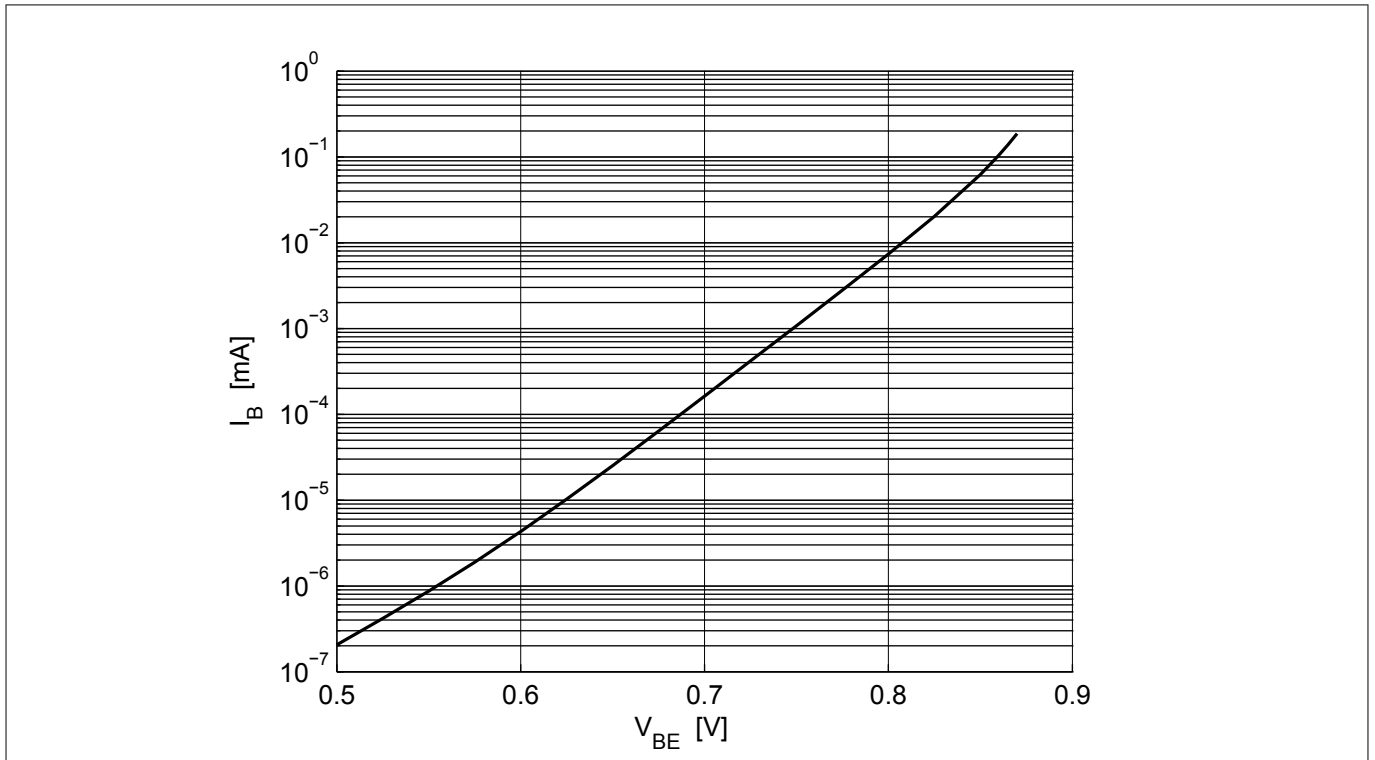


**Figure 4 DC current gain  $h_{FE} = f(I_C)$ ,  $V_{CE} = 1.8 V$**

**Electrical characteristics**

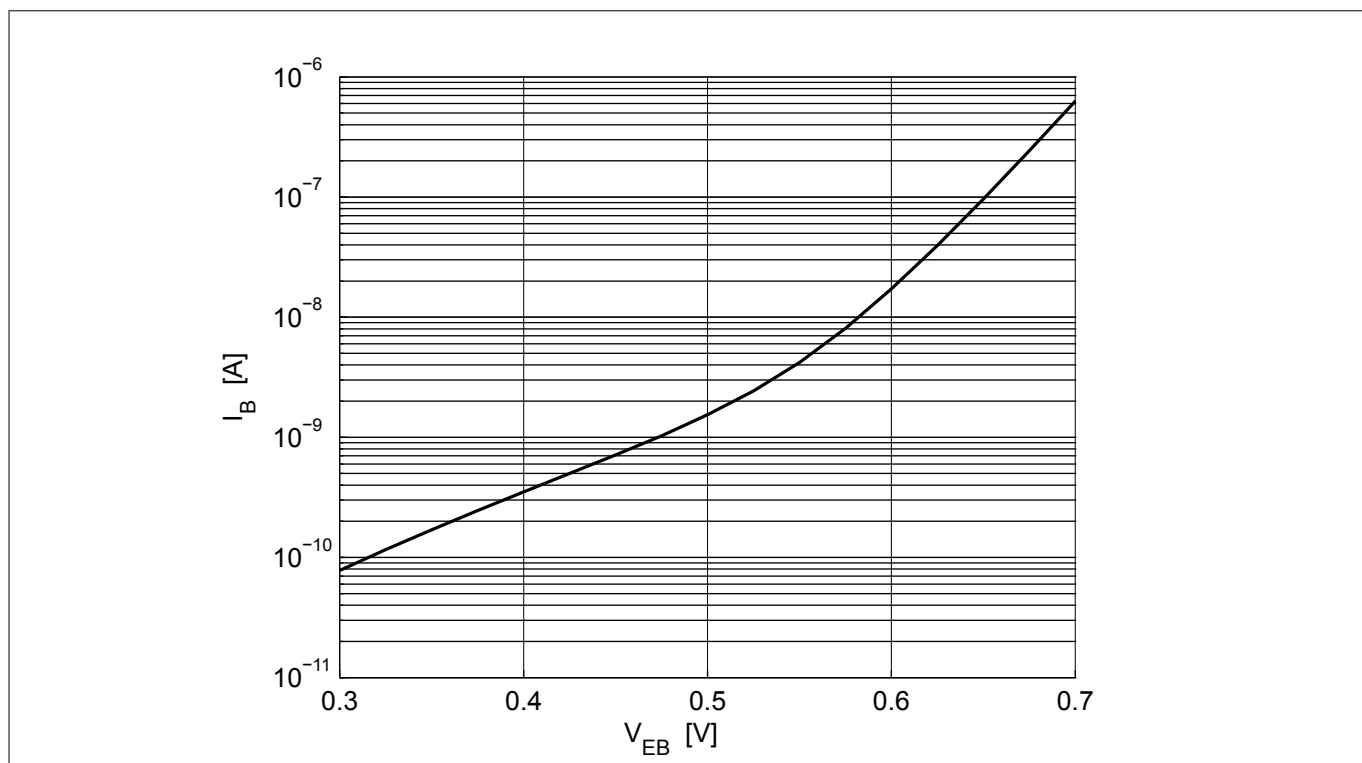


**Figure 5** Collector current vs. base emitter forward voltage  $I_C = f(V_{BE})$ ,  $V_{CE} = 1.8$  V



**Figure 6** Base current vs. base emitter forward voltage  $I_B = f(V_{BE})$ ,  $V_{CE} = 1.8$  V

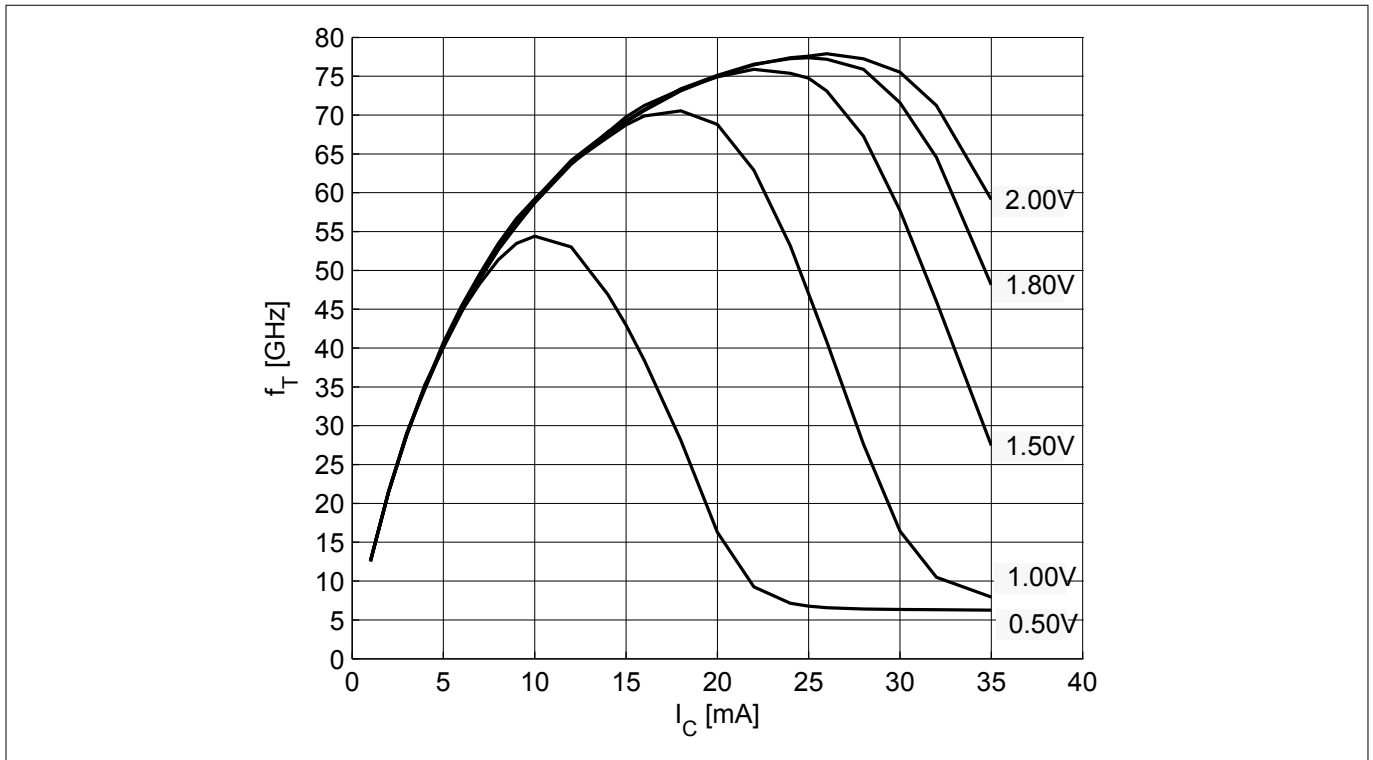
**Electrical characteristics**



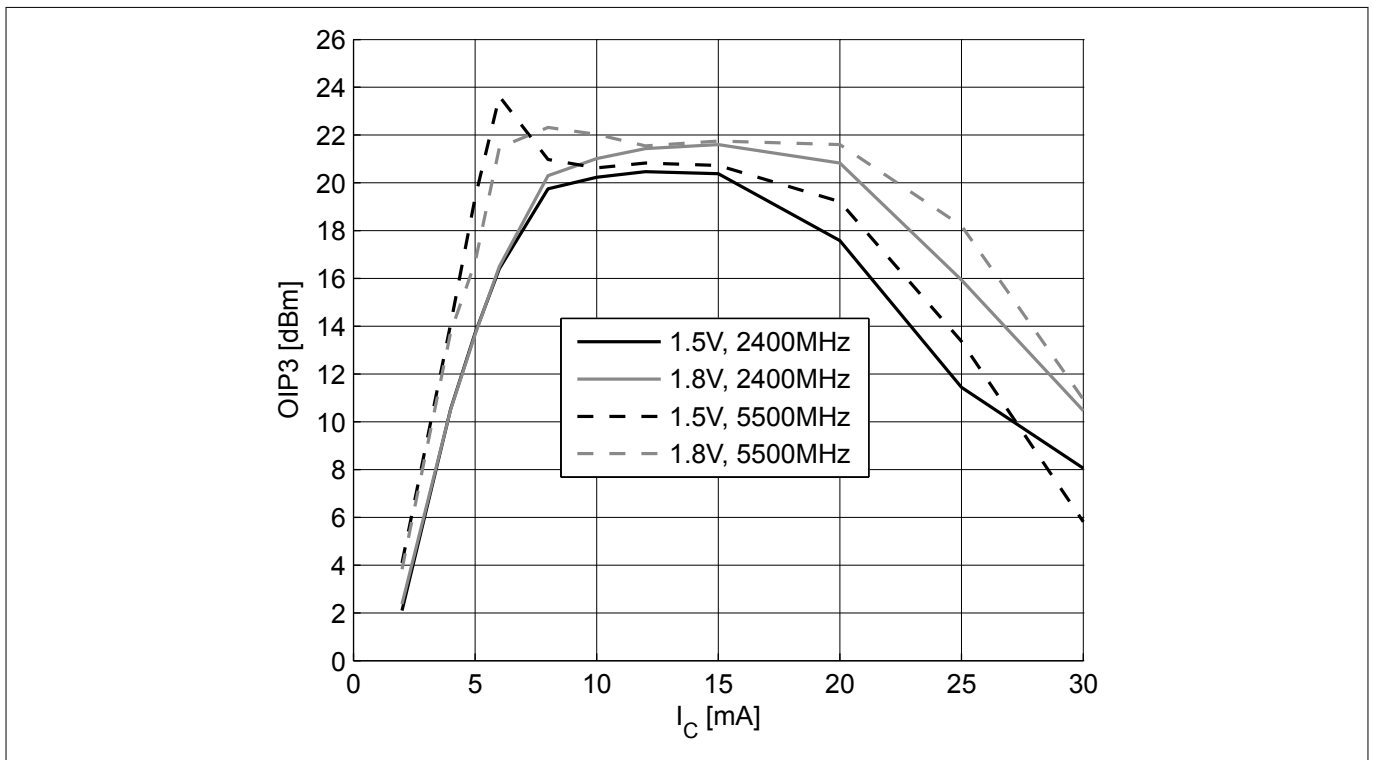
**Figure 7** Base current vs. base emitter reverse voltage  $I_B = f(V_{EB})$ ,  $V_{CE} = 1.8$  V

Electrical characteristics

**3.5 Characteristic AC diagrams**

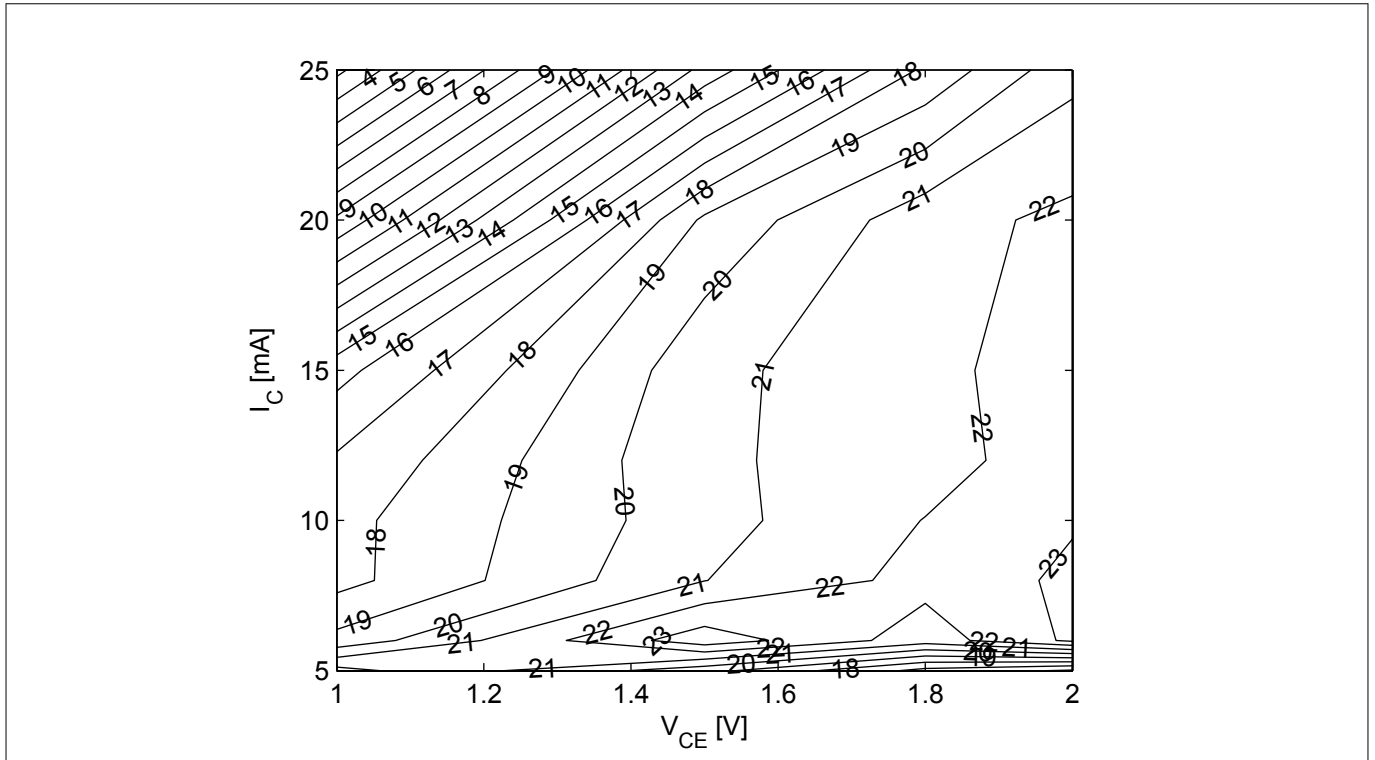


**Figure 8** Transition frequency  $f_T = f(I_C)$ ,  $f = 2$  GHz,  $V_{CE} =$  parameter

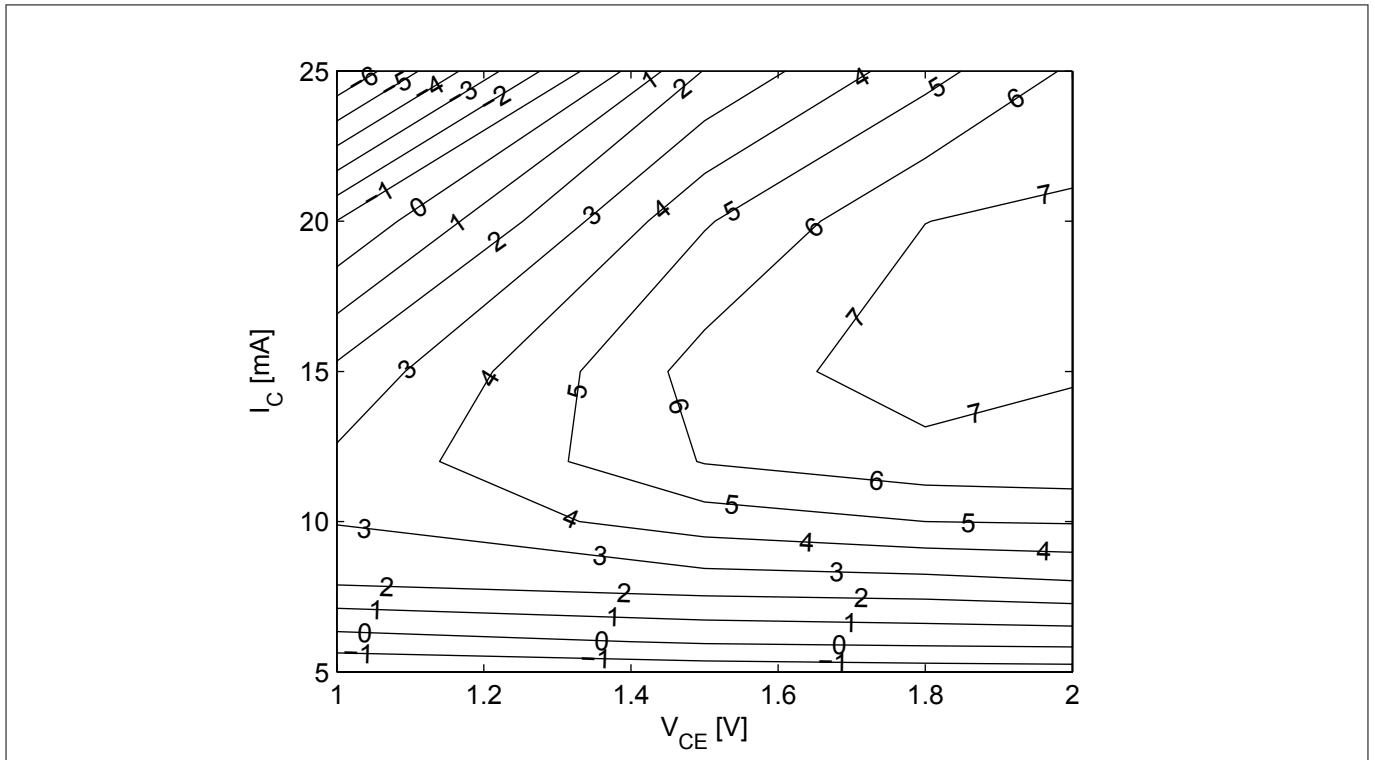


**Figure 9** 3rd order intercept point at output  $OIP_3 = f(I_C)$ ,  $Z_S = Z_L = 50 \Omega$ ,  $V_{CE}$ ,  $f =$  parameters

**Electrical characteristics**

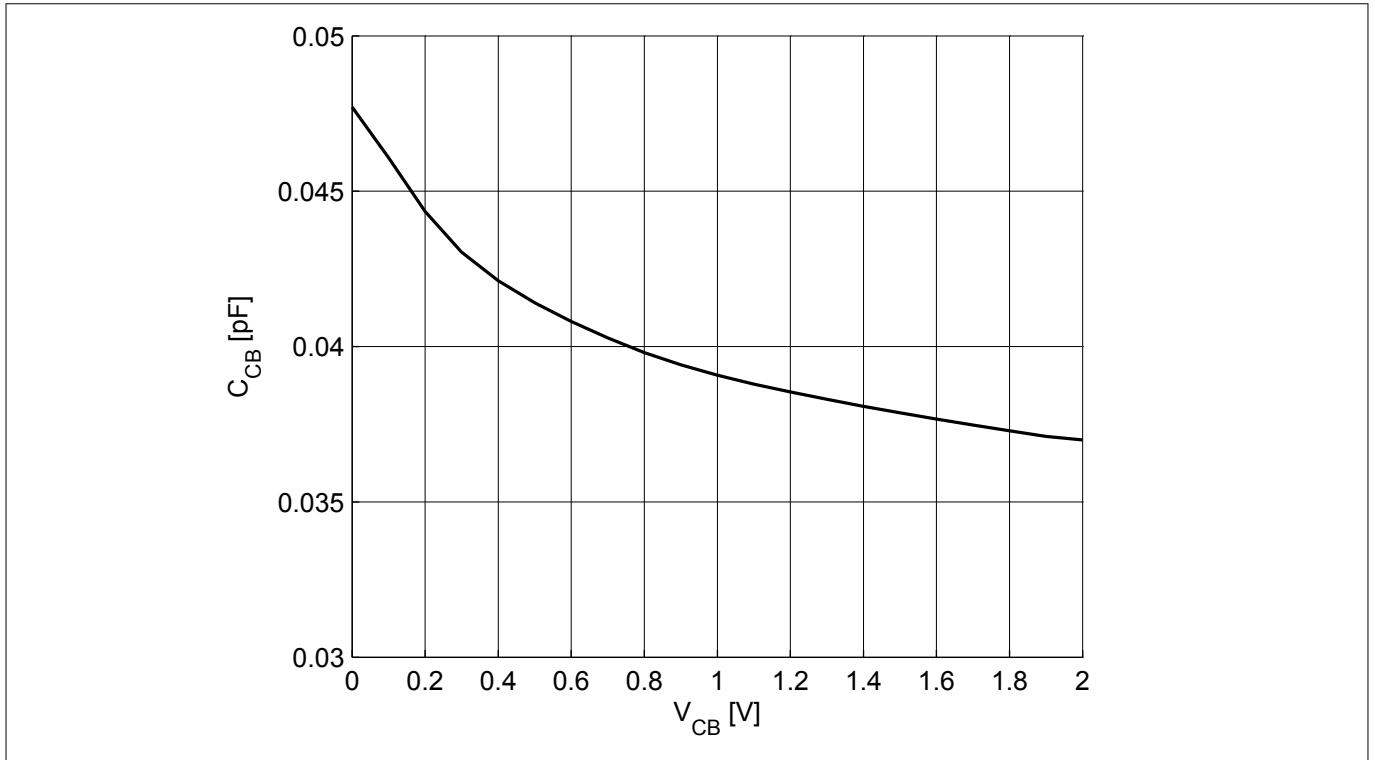


**Figure 10** 3rd order intercept point at output  $OIP_3$  [dBm] =  $f(I_C, V_{CE})$ ,  $Z_S = Z_L = 50 \Omega$ ,  $f = 5.5$  GHz

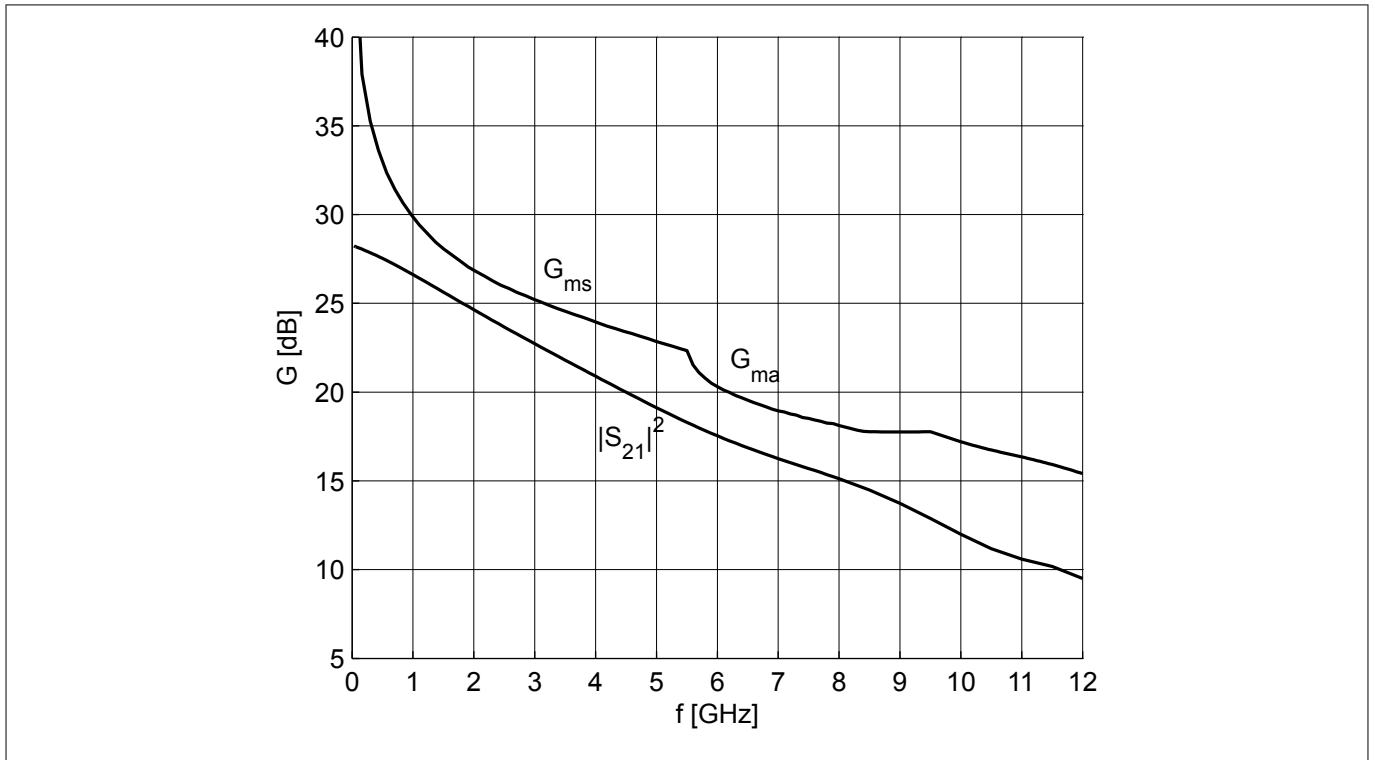


**Figure 11** Compression point at output  $OP_{1dB}$  [dBm] =  $f(I_C, V_{CE})$ ,  $Z_S = Z_L = 50 \Omega$ ,  $f = 5.5$  GHz

**Electrical characteristics**

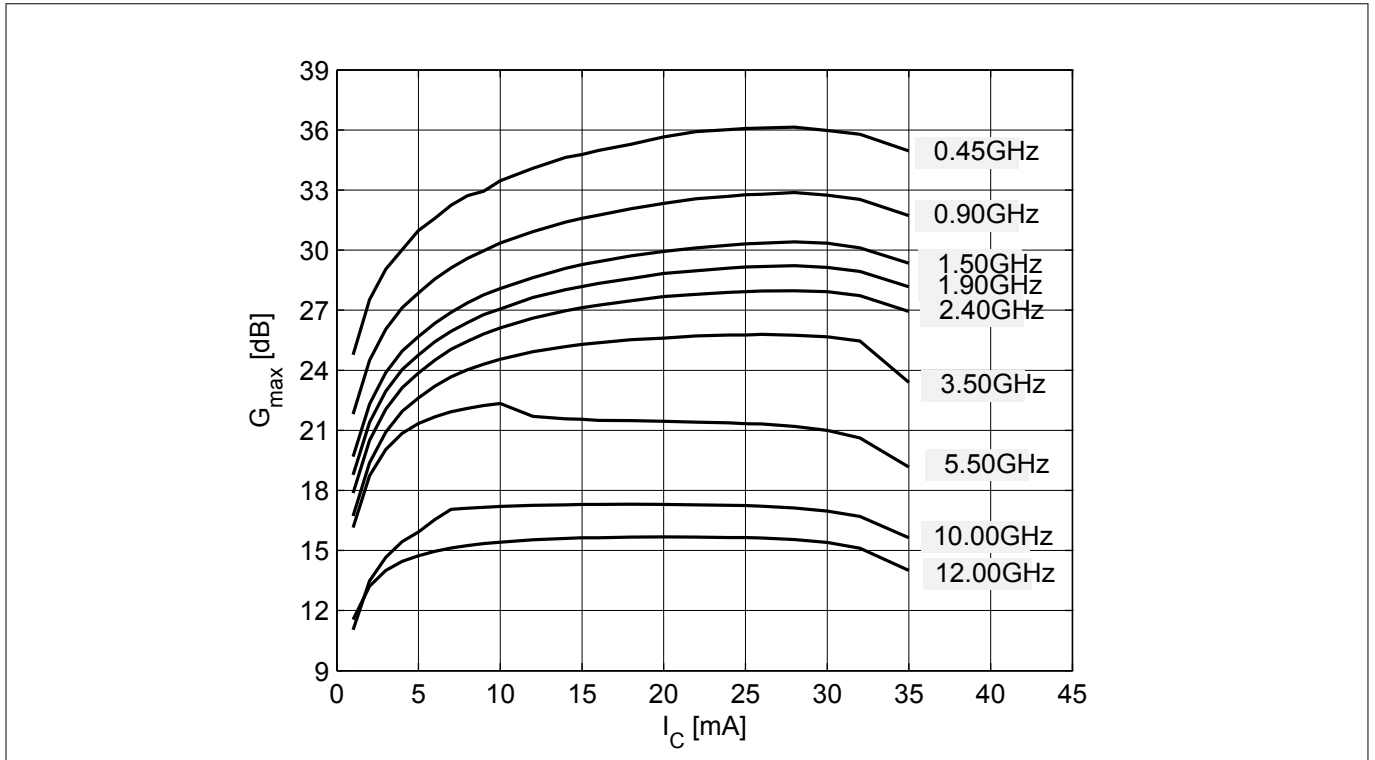


**Figure 12** Collector base capacitance  $C_{CB} = f(V_{CB})$ ,  $f = 1$  MHz

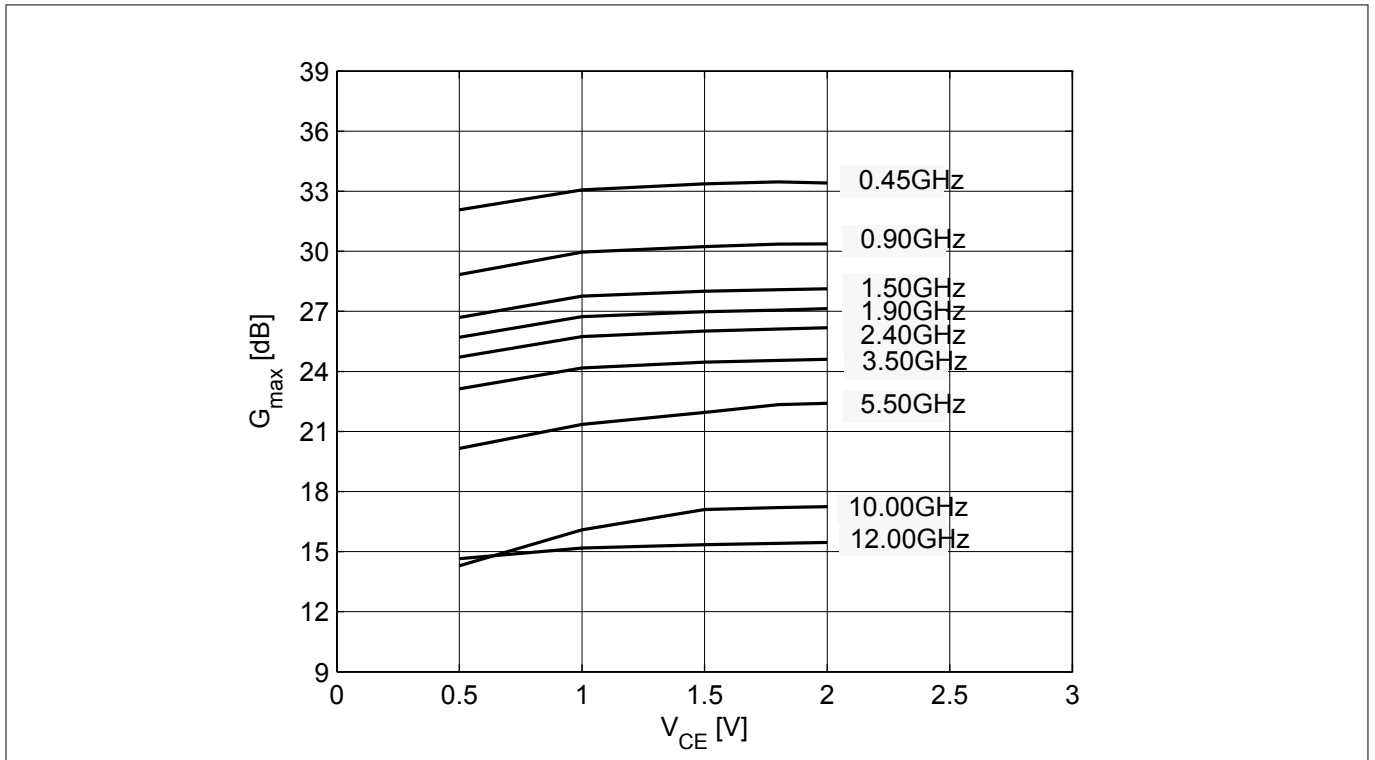


**Figure 13** Gain  $G_{ma}$ ,  $G_{ms}$ ,  $|S_{21}|^2 = f(f)$ ,  $V_{CE} = 1.8$  V,  $I_C = 10$  mA

**Electrical characteristics**

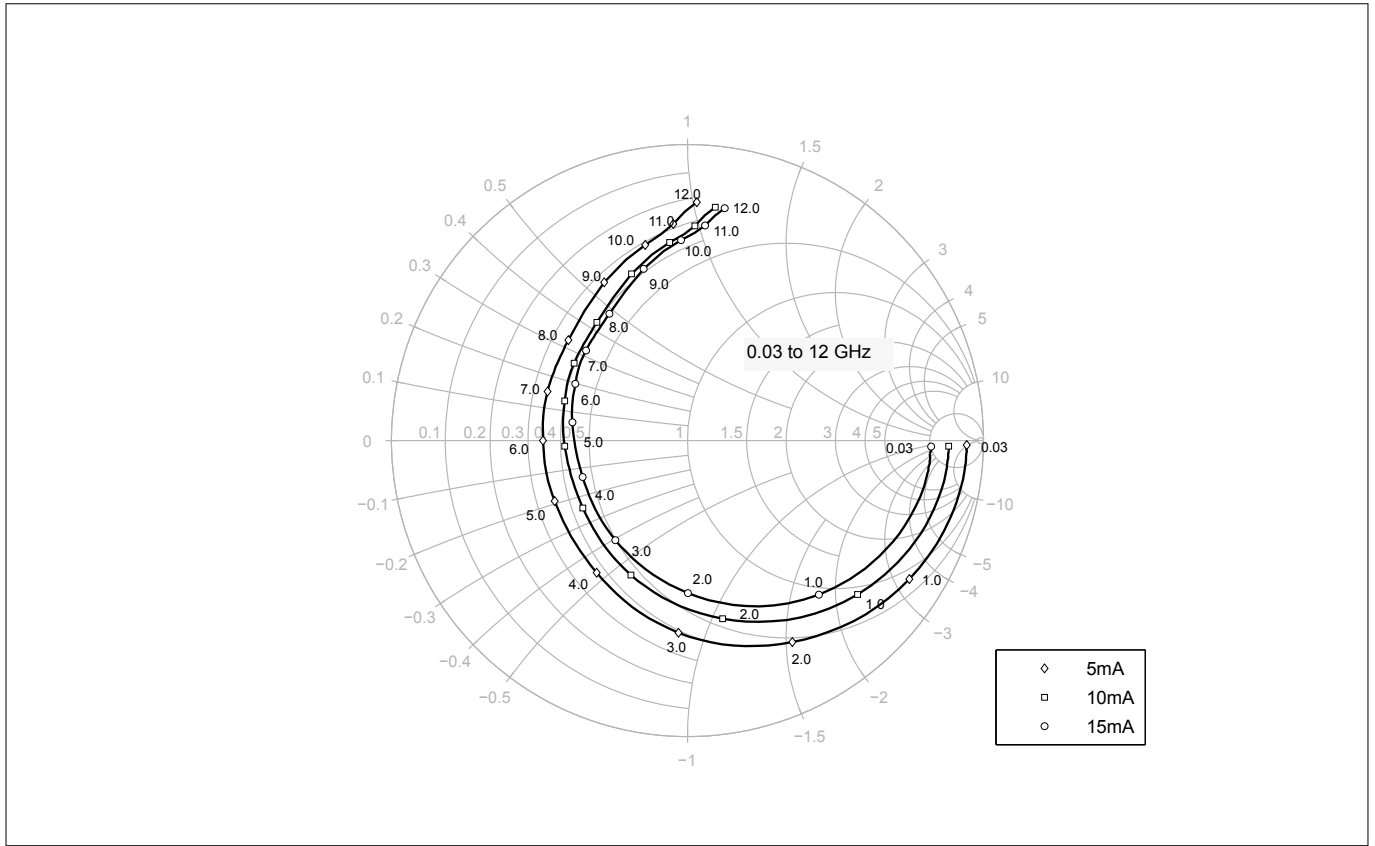


**Figure 14** Maximum power gain  $G_{max} = f(I_C)$ ,  $V_{CE} = 1.8$  V,  $f =$  parameter in GHz

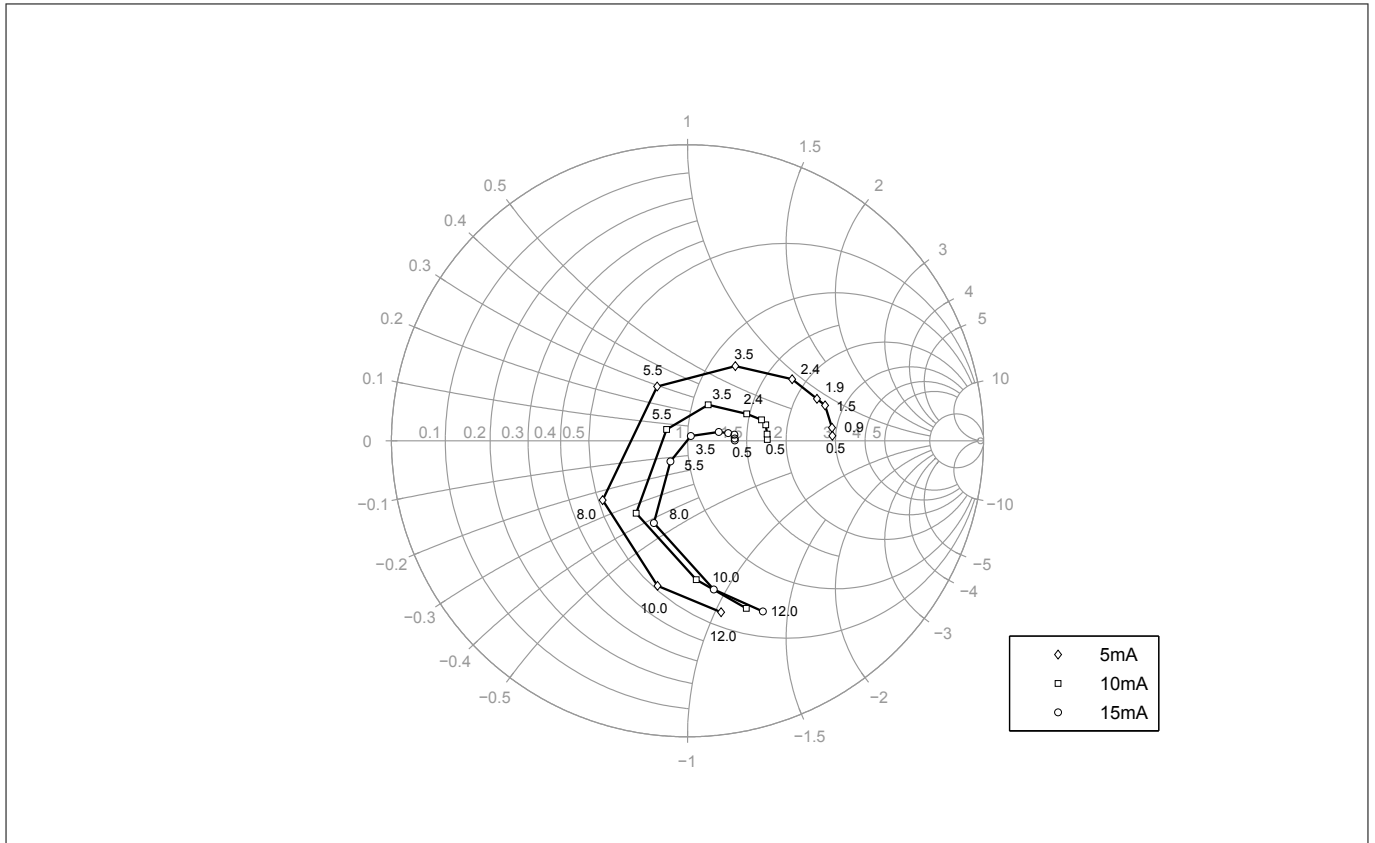


**Figure 15** Maximum power gain  $G_{max} = f(V_{CE})$ ,  $I_C = 10$  mA,  $f =$  parameter in GHz

**Electrical characteristics**

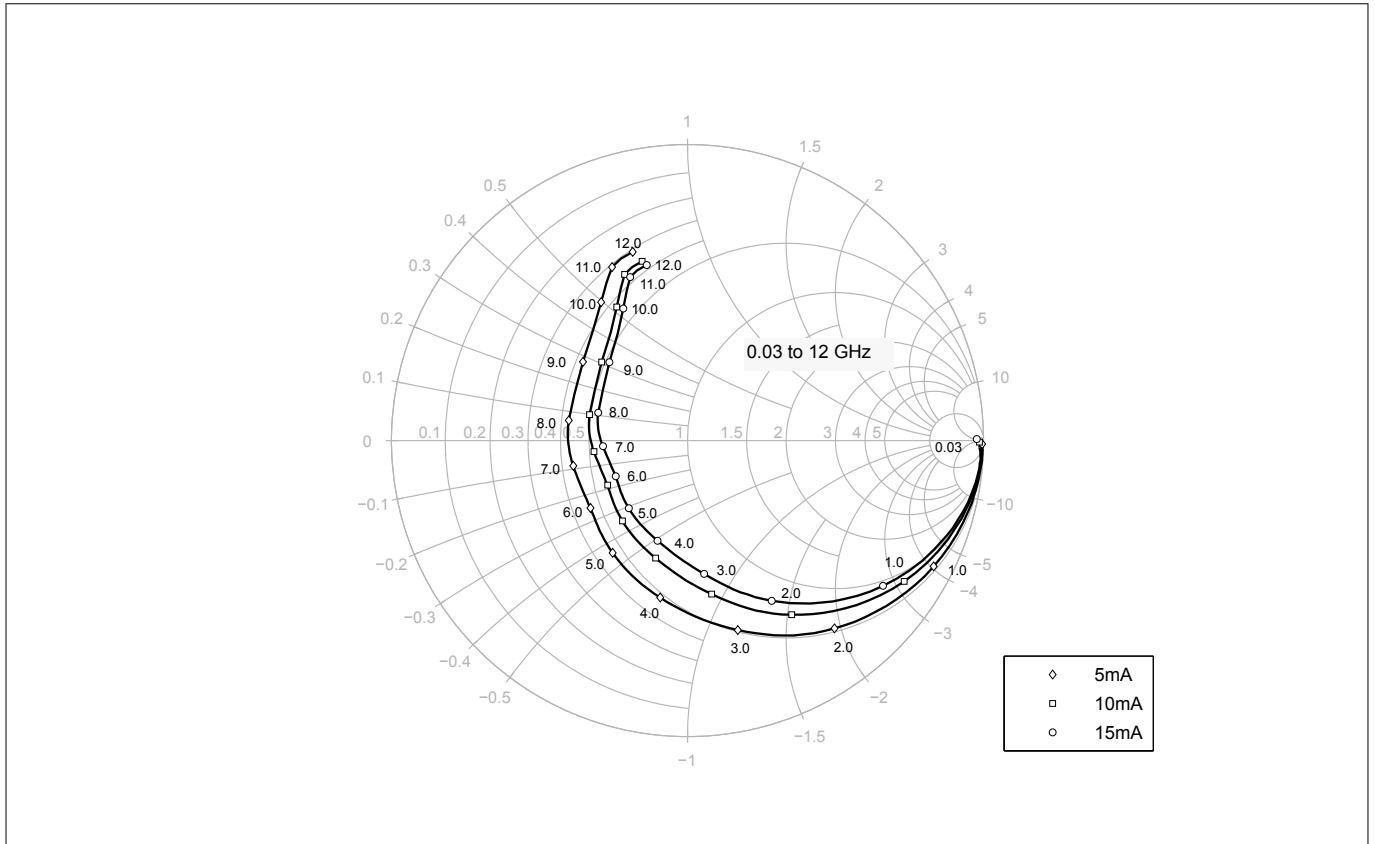


**Figure 16** Input reflection coefficient  $S_{11} = f(f)$ ,  $V_{CE} = 1.8 \text{ V}$ ,  $I_C = 5 / 10 / 15 \text{ mA}$



**Figure 17** Source impedance for minimum noise figure  $Z_{S,opt} = f(f)$ ,  $V_{CE} = 1.8 \text{ V}$ ,  $I_C = 5 / 10 / 15 \text{ mA}$

**Electrical characteristics**

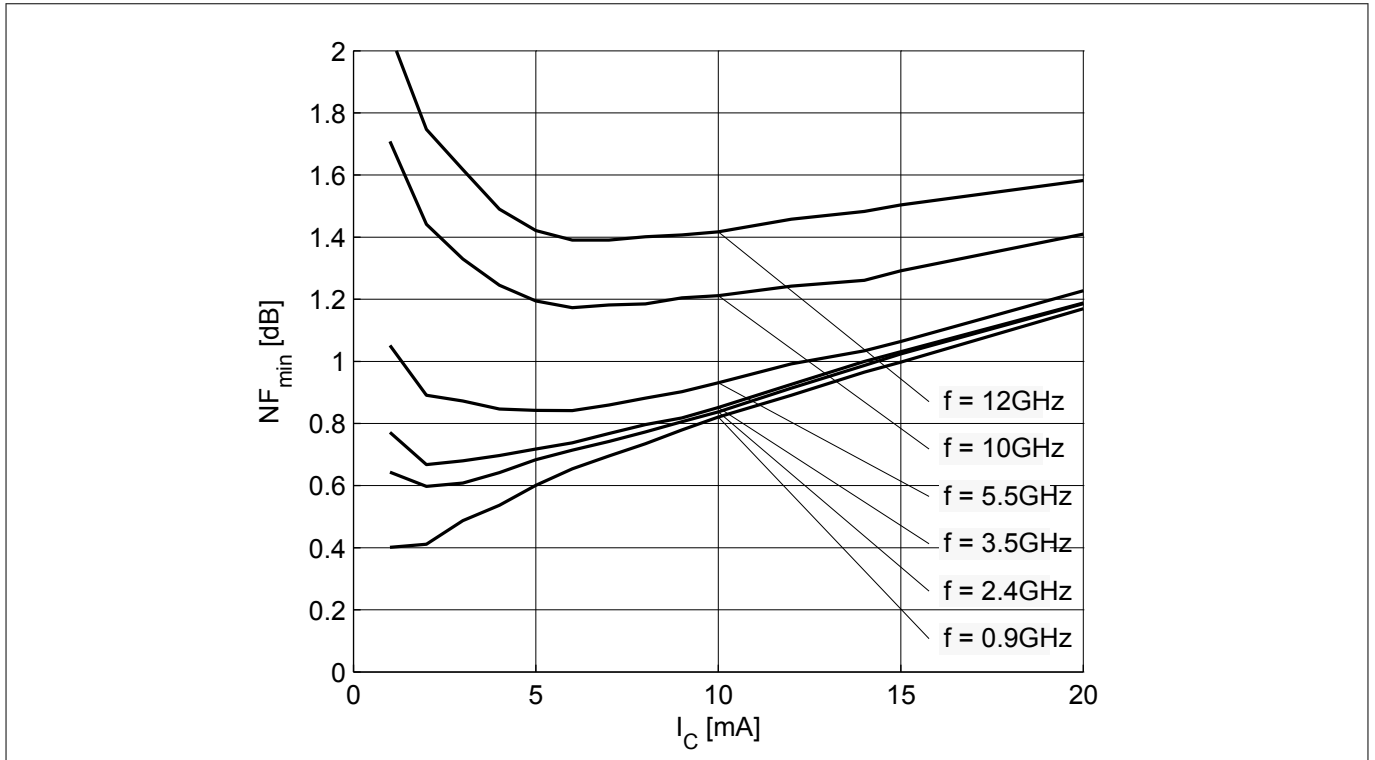


**Figure 18** Output reflection coefficient  $S_{22} = f(f)$ ,  $V_{CE} = 1.8 \text{ V}$ ,  $I_C = 5 / 10 / 15 \text{ mA}$

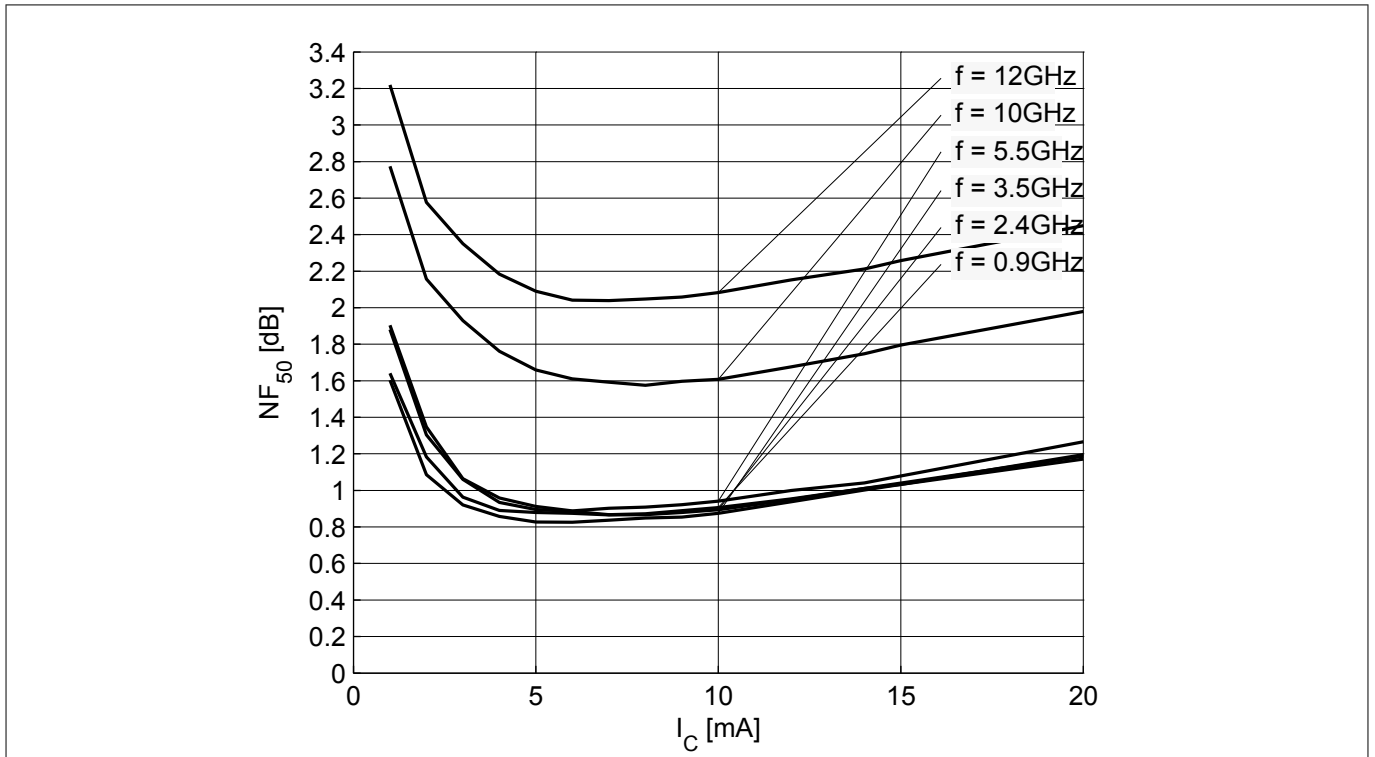


**Figure 19** Noise figure  $NF_{min} = f(f)$ ,  $V_{CE} = 1.8 \text{ V}$ ,  $Z_S = Z_{S,opt}$ ,  $I_C = 5 / 10 / 15 \text{ mA}$

**Electrical characteristics**



**Figure 20** Noise figure  $NF_{min} = f(I_C)$ ,  $V_{CE} = 1.8 V$ ,  $Z_S = Z_{opt}$ ,  $f =$  parameter in GHz



**Figure 21** Noise figure  $NF_{50} = f(I_C)$ ,  $V_{CE} = 1.8 V$ ,  $Z_S = 50 \Omega$ ,  $f =$  parameter in GHz

*Note:* The curves shown in this chapter have been generated using typical devices but shall not be considered as a guarantee that all devices have identical characteristic curves.  $T_A = 25^\circ C$ .



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Revision history

## Revision history

Document version	Date of release	Description of changes
2.0	2018-09-26	New datasheet layout.

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